

ABSTRACT OF THE DISCLOSURE

Provided is a 3-5 group compound semiconductor comprising a GaAs substrate, a buffer layer on said GaAs substrate and an epitaxial crystal layer on said buffer layer, and the dislocation density in the epitaxial crystal layer on said buffer layer is  $2000/\text{cm}^2$  or less. The properties and reliability of an electronic device or optical device can be remarkably improved.